The following Listing of Claims will replace all prior versions, and listings, of claims in the present application:

Listing of Claims:

1. (Currently amended) A method for making a dielectric structure for dual-damascene applications, the method comprising:

(a) providing a substrate;

(b) fabricating first metallization lines ~~within~~ in the substrate;

(c) forming a barrier layer over the first metallization lines and the substrate; and

(d) forming an inter-metal dielectric structure, the forming of the inter-metal dielectric structure,

consisting of:

(d)(i) forming an inorganic dielectric layer ~~to a thickness of between about 0.4 microns (μ) and 0.5 microns~~ to define a via dielectric layer directly over the barrier layer, the inorganic dielectric layer ~~having a dielectric constant of about 4 and~~ being highly selective relative to the barrier layer when etched; and

(d)(ii) forming a carbon doped oxide layer ~~to a thickness of between about 0.5 microns and 0.6 microns~~ to define a trench dielectric layer that is defined directly over and in direct contact with the inorganic dielectric layer, the trench layer being formed to define a metallization line layer of the inter-metal dielectric structure.

2. (Previously Presented) A method for making a dielectric structure for dual-damascene applications as recited in claim 1, further comprising:

forming a trench in the carbon doped oxide layer using a first etch chemistry.

3. (Currently amended) A method for making a dielectric structure for dual-damascene applications as recited in claim 2, further comprising:

forming a via in the inorganic dielectric layer using a second etch chemistry, the second etch chemistry being different than the first etch chemistry and the via being formed from within the trench.

4. (Original) A method for making a dielectric structure for dual-damascene applications as recited in claim 1, wherein the barrier layer is one of a silicon nitride layer and a silicon carbide layer.

5. (Currently amended) A method for making a dielectric structure for dual-damascene applications as recited in ~~claim 4~~ claim 1, wherein the forming of the inorganic dielectric layer includes,

depositing a TEOS silicon dioxide material over the barrier layer.

6. (Currently amended) A method for making a dielectric structure for dual-damascene applications as recited in ~~claim 5~~ claim 1, wherein the carbon doped oxide layer is a low dielectric constant layer having a dielectric constant of about and no greater than 3.0.

7. (Previously Presented) A method for making a dielectric structure for dual-damascene applications as recited in claim 3, wherein the inorganic dielectric layer is one of a TEOS oxide layer and a fluorine doped oxide layer.

8. (Currently amended) A method for making a dielectric structure for dual-damascene applications as recited in claim 7, wherein the first etch chemistry is optimized to

etch through the carbon doped oxide layer and the second etch chemistry is optimized to etch through one of the TEOS oxide layer ~~or~~ and the fluorine doped oxide layer.

9. (Original) A method for making a dielectric structure for dual-damascene applications as recited in claim 8, wherein the second etch chemistry is selective to the barrier layer.

10-32. Canceled.

33. (New) A method for making a dielectric structure for dual-damascene applications as recited in claim 1, wherein the inorganic dielectric layer has a thickness between about 0.4 microns (μ) and 0.5 microns

34. (New) A method for making a dielectric structure for dual-damascene applications as recited in claim 1, wherein the carbon doped oxide layer has a thickness between about 0.5 microns and 0.6 microns.

35. (New) A method for making a dielectric structure for dual-damascene applications as recited in claim 1, wherein the inorganic dielectric layer has a dielectric constant of about 4.